

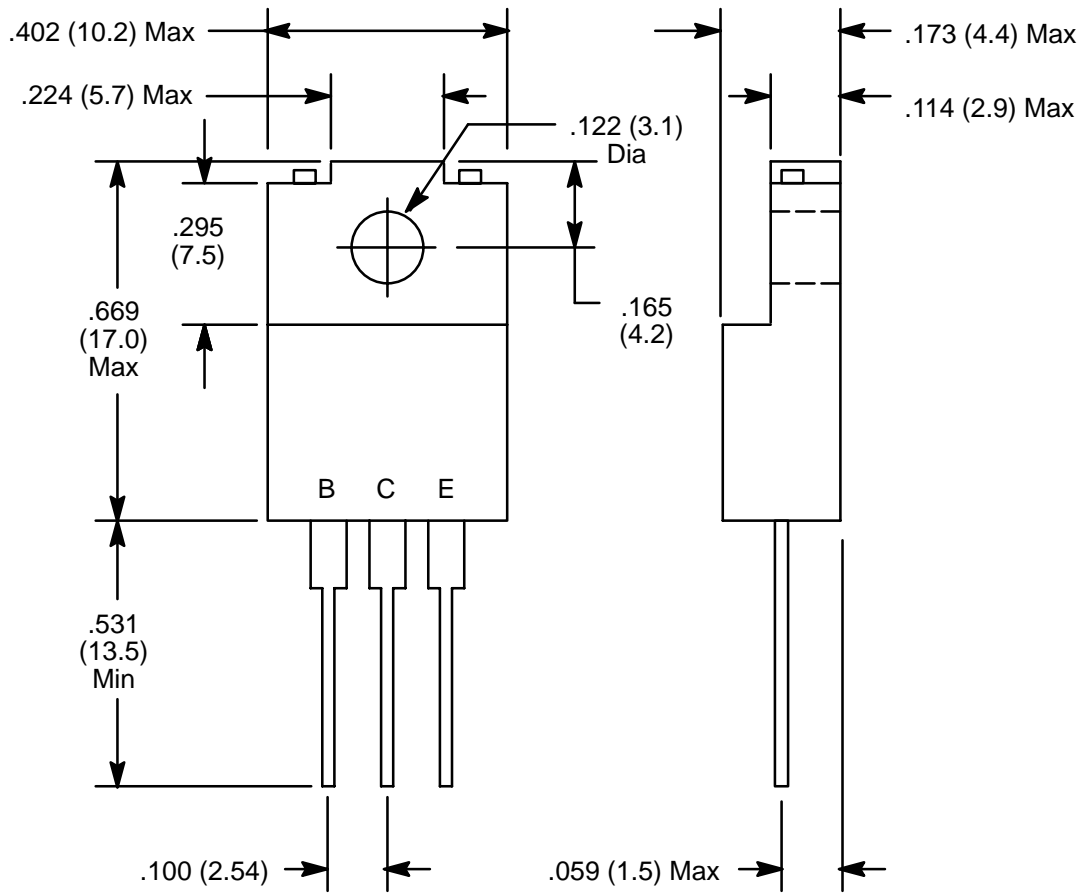
NTE2576 (NPN) & NTE2577 (PNP) Silicon Complementary Transistors Audio Output Driver

Absolute Maximum Ratings: ($T_A = +25^\circ\text{C}$ unless otherwise specified)

Collector–Base Voltage, V_{CB0}	180V
Collector–Emitter Voltage, V_{CEO}	180V
Emitter–Base Voltage, V_{EBO}	6V
Collector Current, I_C	2A
Base Current, I_B	1A
Power Dissipation ($T_C = +25^\circ\text{C}$), P_C	20W
Operating Junction Temperature, T_J	+150°C
Storage Temperature Range, T_{stg}	–55° to +150°C

Electrical Characteristics: ($T_A = +25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cutoff Current	I_{CBO}	$V_{CB} = 180\text{V}$	–	–	10	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = 6\text{V}$	–	–	10	μA
Collector–Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 10\text{mA}$	180	–	–	V
DC Current Gain	h_{FE}	$V_{CE} = 10\text{V}, I_C = 700\text{mA}$	60	–	240	
Collector–Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 700\text{mA}, I_B = 70\text{mA}$	–	–	1.0	V
Transition Frequency	f_T	$V_{CE} = 12\text{V}, I_E = 700\text{mA}$	–	60	–	MHz
Output Capacitance	C_{ob}	$V_{CB} = 10\text{V}, f = 1\text{MHz}$	–	30	–	pF



NOTE: Tab is isolated